





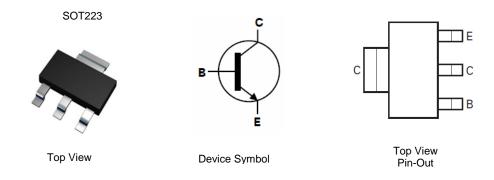
60V NPN HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- BV_{CFO} > 60V
- I_C = 3A High Continuous Current
- I_{CM} = 6A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 300mV @ 1A
- Complementary PNP Type: FZT751
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.112 grams (Approximate)



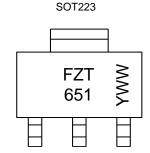
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT651TA	AEC-Q101	FZT651	7	12	1,000
FZT651TC	AEC-Q101	FZT651	13	12	4,000

Notes:

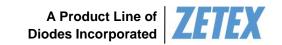
- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 651 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	lc	3	Α
Peak Pulse Current	I _{CM}	6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D	2	W
Power Dissipation	(Note 6)	P _D	3	W
Thermal Resistance, Junction to Ambient	(Note 5)	В	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	41.7	°C/W
Thermal Resistance, Junction to Leads (Note	$R_{ heta JL}$	12.9	°C/W	
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 8)

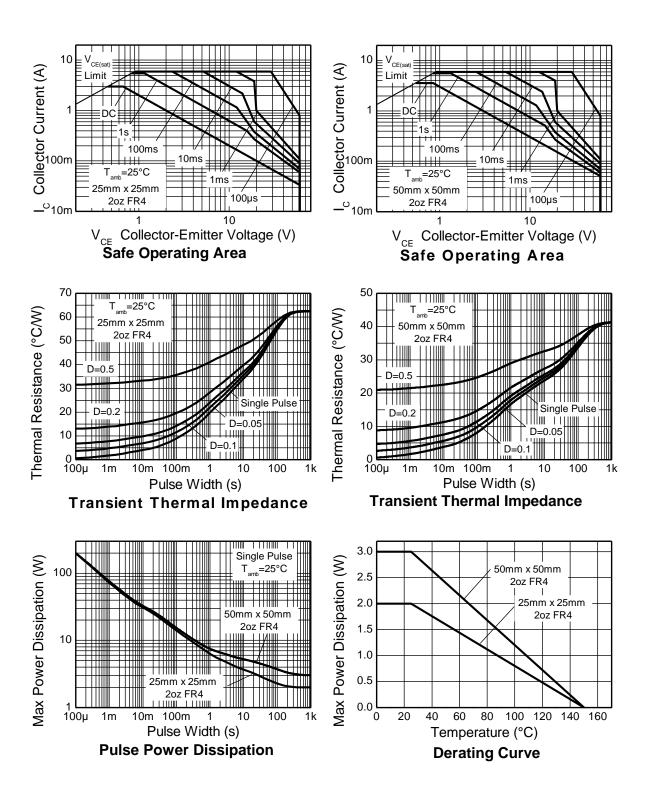
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

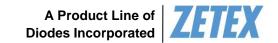
- 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information







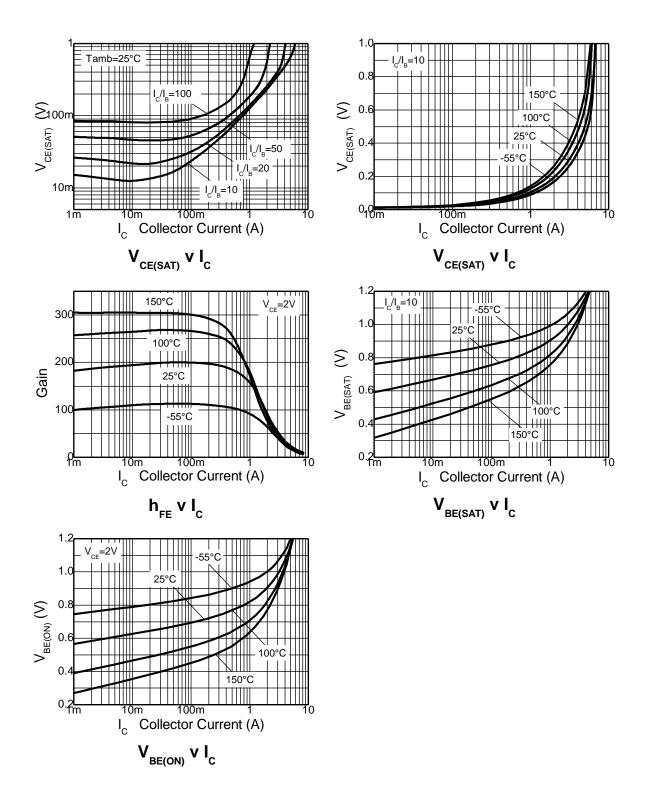
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	_	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	_	-	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	-	V	$I_{E} = 100 \mu A$
Collector Cut-Off Current		-	_	0.1	μΑ	$V_{CB} = 60V$
Collector Cut-Off Current	I _{CBO}	-	_	10		V _{CB} = 60V, T _A = +125°C
Emitter Cut-Off Current	I _{EBO}	-	_	100	nA	V _{EB} = 4V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	-	0.12	0.3	V	$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 9)		-	0.43	0.6	V	$I_C = 3A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	-	0.9	1.25	V	$I_C = 1A, I_B = 100mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	-	0.8	1.0	V	I _C = 1A, V _{CE} = 2V
	h _{FE}	70	200	-		I _C = 50mA, V _{CE} = 2V
DC Current Coin (Note 0)		100	200	300		I _C = 500mA, V _{CE} = 2V
DC Current Gain (Note 9)		80	170	-	_	I _C = 1A, V _{CE} = 2V
		40	80	-		$I_C = 2A$, $V_{CE} = 2V$
Current Gain-Bandwidth Product (Note 9)	f _T	140	175	-	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Switching Times	ton	-	45	-	ns	$I_C = 500 \text{mA}, V_{CC} = 10 \text{V},$
Switching filles	t _{off}	-	800	-	115	$I_{B1} = I_{B2} = 50 \text{mA}$
Output Capacitance (Note 9)	C_{obo}	-	_	30	pF	V _{CB} = 10V, f = 1MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



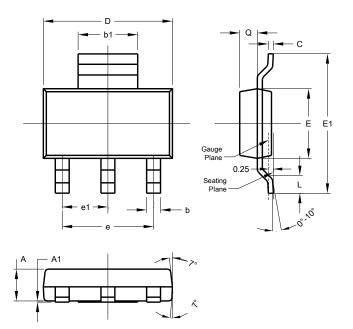
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Package Outline Dimensions

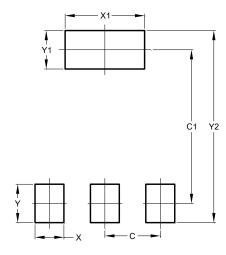
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

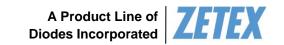
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8 00





March 2015

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